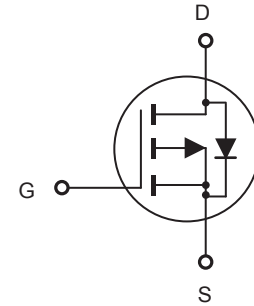
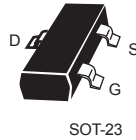


P-Channel Enhancement Mode Field Effect Transistor

FEATURES

- -30V, -3.8A, $R_{DS(ON)} = 55m\Omega$ @ $V_{GS} = -10V$.
 $R_{DS(ON)} = 86m\Omega$ @ $V_{GS} = -4.5V$.
- High dense cell design for extremely low $R_{DS(ON)}$.
- Rugged and reliable.
- Lead free product is acquired.
- SOT-23 package.



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Limit | Units |
|---------------------------------------|----------------|------------|------------------|
| Drain-Source Voltage | V_{DS} | -30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | -3.8 | A |
| Drain Current-Pulsed ^a | I_{DM} | -15.2 | A |
| Maximum Power Dissipation | P_D | 1.25 | W |
| Operating and Store Temperature Range | T_J, T_{stg} | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Limit | Units |
|--|-----------------|-------|--------------------|
| Thermal Resistance, Junction-to-Ambient ^b | $R_{\theta JA}$ | 100 | $^\circ\text{C/W}$ |



CES2313A

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Test Condition | Min | Typ | Max | Units |
|---|--------------|--|-----|-----|------|-----------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = -250\mu A$ | -30 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -30V, V_{GS} = 0V$ | | | -1 | μA |
| Gate Body Leakage Current, Forward | I_{GSSF} | $V_{GS} = 20V, V_{DS} = 0V$ | | | 100 | nA |
| Gate Body Leakage Current, Reverse | I_{GSSR} | $V_{GS} = -20V, V_{DS} = 0V$ | | | -100 | nA |
| On Characteristics ^c | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{GS} = V_{DS}, I_D = -250\mu A$ | -1 | | -3 | V |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = -10V, I_D = -3.8A$ | | 45 | 55 | $m\Omega$ |
| | | $V_{GS} = -4.5V, I_D = -3A$ | | 66 | 86 | $m\Omega$ |
| Dynamic Characteristics ^d | | | | | | |
| Forward Transconductance | g_{FS} | $V_{DS} = -15V, I_D = -3.8A$ | | 4 | | S |
| Input Capacitance | C_{iss} | $V_{DS} = -15V, V_{GS} = 0V, f = 1.0\text{ MHz}$ | | 640 | | pF |
| Output Capacitance | C_{oss} | | | 135 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | | 95 | | pF |
| Switching Characteristics ^d | | | | | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -15V, I_D = -1A, V_{GS} = -10V, R_{GEN} = 6\Omega$ | | 11 | 20 | ns |
| Turn-On Rise Time | t_r | | | 5 | 10 | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 30 | 60 | ns |
| Turn-Off Fall Time | t_f | | | 7 | 14 | ns |
| Total Gate Charge | Q_g | $V_{DS} = -15V, I_D = -3.8A, V_{GS} = -10V$ | | 13 | 17 | nC |
| Gate-Source Charge | Q_{gs} | | | 2 | | nC |
| Gate-Drain Charge | Q_{gd} | | | 3 | | nC |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| Drain-Source Diode Forward Current ^b | I_S | | | | -3.8 | A |
| Drain-Source Diode Forward Voltage ^c | V_{SD} | $V_{GS} = 0V, I_S = -3.8A$ | | | -1.3 | V |
| Notes : □ a.Repetitive Rating : Pulse width limited by maximum junction temperature.□ b.Surface Mounted on FR4 Board, $t < 5\text{ sec.}$ □ c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.□ d.Guaranteed by design, not subject to production testing.□ □ | | | | | | |



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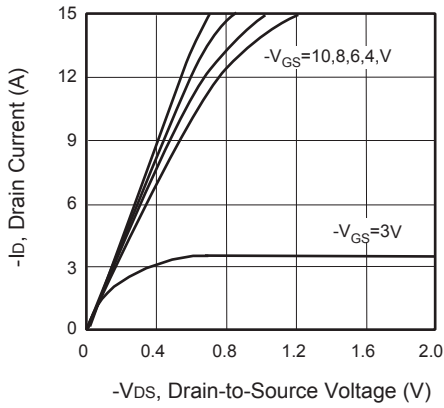


Figure 1. Output Characteristics

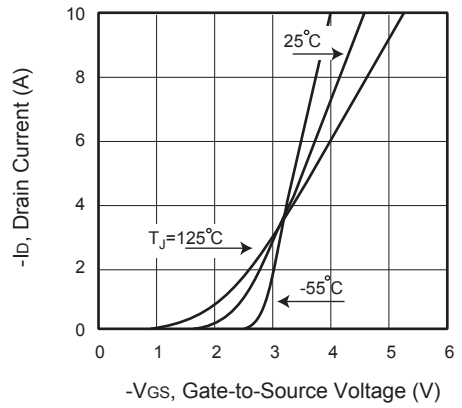


Figure 2. Transfer Characteristics

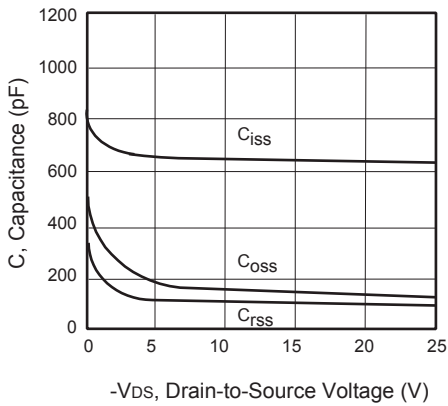


Figure 3. Capacitance

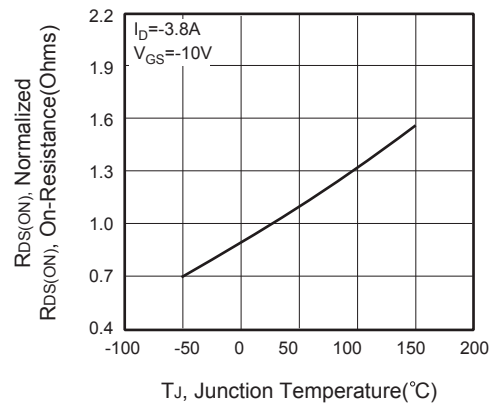


Figure 4. On-Resistance Variation with Temperature

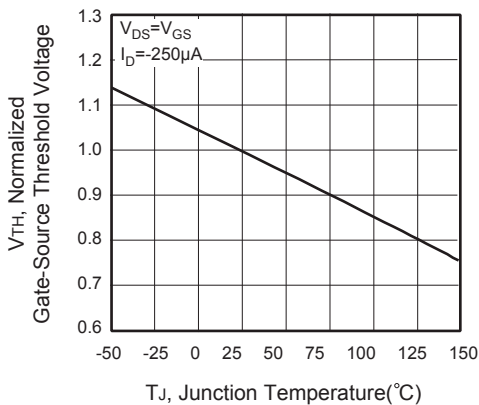


Figure 5. Gate Threshold Variation with Temperature

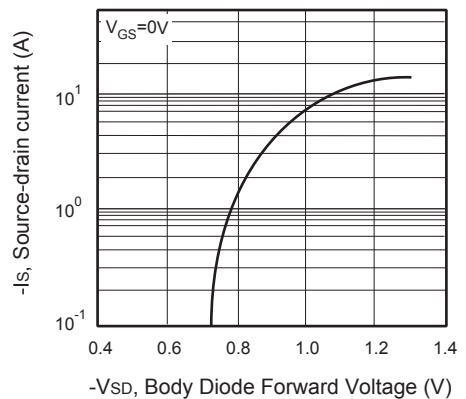


Figure 6. Body Diode Forward Voltage Variation with Source Current



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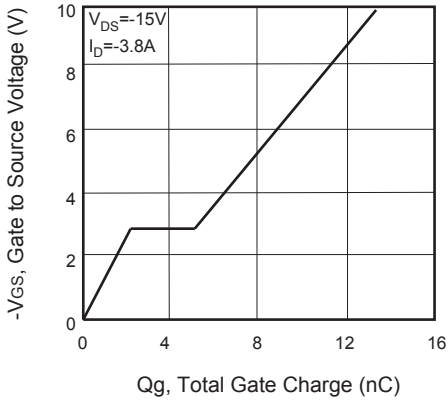


Figure 7. Gate Charge

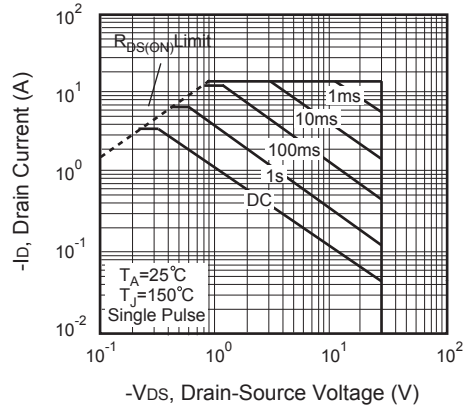


Figure 8. Maximum Safe Operating Area

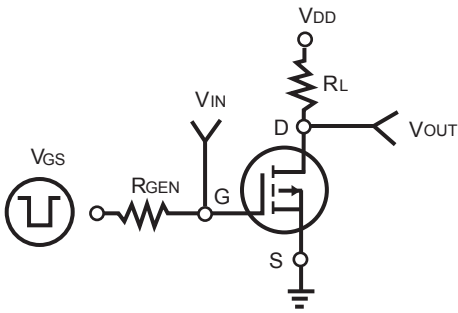


Figure 9. Switching Test Circuit



Figure 10. Switching Waveforms

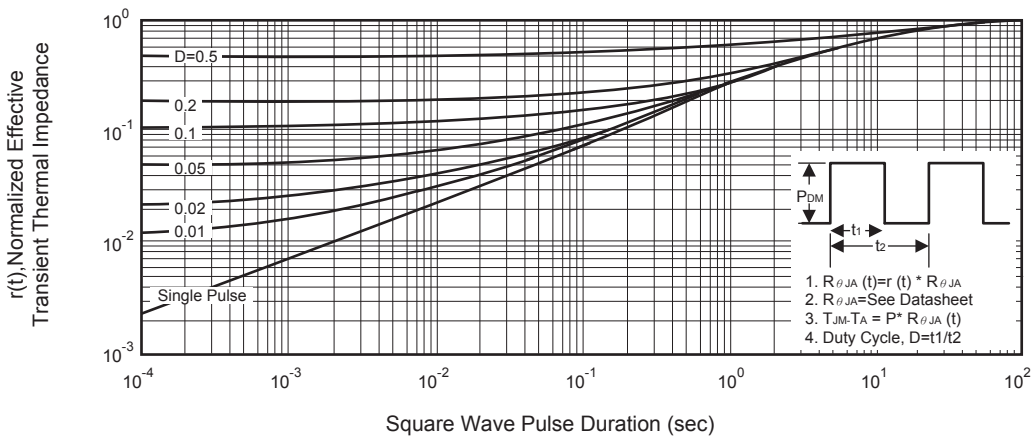


Figure 11. Normalized Thermal Transient Impedance Curve